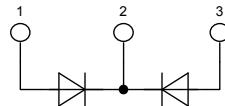


HiPerFRED²

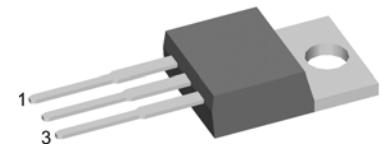
High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Common Cathode

Part number

DPG 30 C 300 PB



V_{RRM} = 300 V
I_{FAV} = 2x 15 A
t_{rr} = 35 ns



Backside: cathode

Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm}-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package:

- Housing: TO-220
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

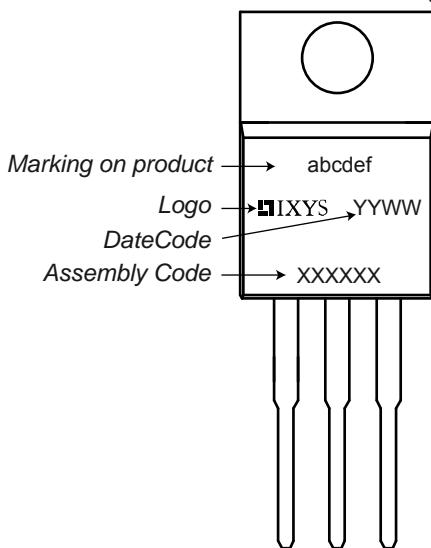
Symbol	Definition	Conditions		Ratings		
		min.	typ.	max.	Unit	
V _{RRM}	max. repetitive reverse voltage			300	V	
I _R	reverse current	V _R = 300V	T _{VJ} = 25°C		1	µA
		V _R = 300V	T _{VJ} = 150°C		0.08	mA
V _F	forward voltage	I _F = 15A	T _{VJ} = 25°C		1.26	V
		I _F = 30A			1.51	V
		I _F = 15A	T _{VJ} = 150°C		1.01	V
		I _F = 30A			1.29	V
I _{FAV}	average forward current	rectangular	d = 0.5	T _C = 140°C		A
V _{F0} r _F	threshold voltage slope resistance } for power loss calculation only			T _{VJ} = 175°C	0.69	V
					18	mΩ
R _{thJC}	thermal resistance junction to case				1.70	K/W
T _{VJ}	virtual junction temperature			-55	175	°C
P _{tot}	total power dissipation			T _C = 25°C	90	W
I _{FSM}	max. forward surge current	t = 10 ms (50 Hz), sine		T _{VJ} = 45°C		A
I _{RM}	max. reverse recovery current			T _{VJ} = 25°C	3	A
		I _F = 15A; V _R = 200V		T _{VJ} = 125°C	6.5	A
		-di _F /dt = 200 A/µs		T _{VJ} = 25°C	35	ns
t _{rr}	reverse recovery time			T _{VJ} = 125°C	55	ns
C _J	junction capacitance	V _R = 150 V; f = 1 MHz		T _{VJ} = 25°C	20	pF

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
I_{RMS}	RMS current	per pin ¹⁾			35	A
R_{thCH}	thermal resistance case to heatsink			0.50		K/W
T_{stg}	storage temperature		-55		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_c	mounting force with clip		20		60	N

¹⁾ I_{RMS} is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.

In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

Product Marking



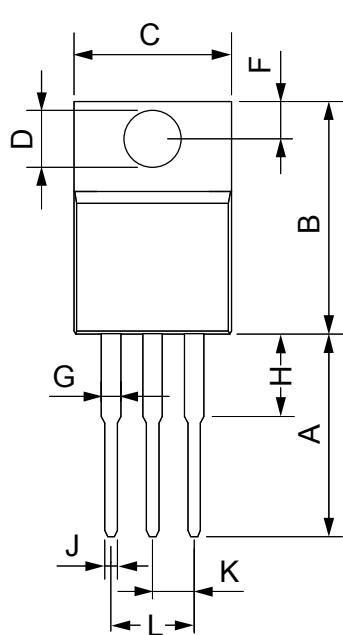
Part number

D = Diode
 P = HiPerFRED
 G = extreme fast
 30 = Current Rating [A]
 C = Common Cathode
 300 = Reverse Voltage [V]
 PB = TO-220AB (3)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DPG 30 C 300 PB	DPG30C300PB	Tube	50	504380

Similar Part	Package	Voltage Class
DPG30C300PC	TO-263AB (D2Pak)	300
DPG30C300HB	TO-247AD (3)	300

Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.35	0.56	0.014	0.022
R	2.29	2.79	0.090	0.110

